

Yuewei Zhang

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

71
papers

49,269
citations

28
h-index

77
g-index

77
ext. papers

54,829
ext. citations

3.8
avg, IF

6.96
L-index

#	Paper	IF	Citations
71	Electric field effect in atomically thin carbon films. <i>Science</i> , 2004 , 306, 666-9	33.3	47045
70	Demonstration of high mobility and quantum transport in modulation-doped $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterostructures. <i>Applied Physics Letters</i> , 2018 , 112, 173502	3.4	192
69	Modulation-doped $\text{Al}_{0.2}\text{Ga}_{0.8}\text{As}/\text{GaAs}$ field-effect transistor. <i>Applied Physics Letters</i> , 2017 , 111, 023502	3.4	188
68	The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 503001	3	123
67	MOCVD grown epitaxial AlGaAs thin film with an electron mobility of 176 cm^2/Vs at room temperature. <i>APL Materials</i> , 2019 , 7, 022506	5.7	115
66	Polarity governs atomic interaction through two-dimensional materials. <i>Nature Materials</i> , 2018 , 17, 999-1004	10.4	107
65	Demonstration of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ double heterostructure field effect transistors. <i>Applied Physics Letters</i> , 2018 , 112, 233503	3.4	97
64	Low-pressure CVD-grown AlGaAs bevel-field-plated Schottky barrier diodes. <i>Applied Physics Express</i> , 2018 , 11, 031101	2.4	81
63	Delta Doped $\beta\text{-GaAs}$ Field Effect Transistors With Regrown Ohmic Contacts. <i>IEEE Electron Device Letters</i> , 2018 , 39, 568-571	4.4	75
62	Interband tunneling for hole injection in III-nitride ultraviolet emitters. <i>Applied Physics Letters</i> , 2015 , 106, 141103	3.4	67
61	Trapping Effects in Si $\delta\text{-GaAs}$ Doped $\beta\text{-GaAs}$ MESFETs on an Fe-Doped $\beta\text{-GaAs}$ Substrate. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1042-1045	4.4	64
60	AlGaIn channel field effect transistors with graded heterostructure ohmic contacts. <i>Applied Physics Letters</i> , 2016 , 109, 133508	3.4	52
59	Breakdown Characteristics of $\beta\text{-Al}_{0.22}\text{Ga}_{0.78}\text{As}/\text{GaAs}$ Field-Plated Modulation-Doped Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1241-1244	4.4	51
58	Tunnel-injected sub-260 nm ultraviolet light emitting diodes. <i>Applied Physics Letters</i> , 2017 , 110, 201102	3.4	48
57	Evaluation of Low-Temperature Saturation Velocity in $\beta\text{-Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ Modulation-Doped Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 1574-1578	2.9	48
56	Tunnel-injected sub 290 nm ultra-violet light emitting diodes with 2.8% external quantum efficiency. <i>Applied Physics Letters</i> , 2018 , 112, 071107	3.4	45
55	High current density 2D/3D MoS_2/GaN Esaki tunnel diodes. <i>Applied Physics Letters</i> , 2016 , 109, 183505	3.4	44

54	MBE-Grown β -Ga ₂ O ₃ -Based Schottky UV-C Photodetectors With Rectification Ratio ~107. <i>IEEE Photonics Technology Letters</i> , 2018 , 30, 2025-2028	2.2	44
53	Design and demonstration of ultra-wide bandgap AlGa _N tunnel junctions. <i>Applied Physics Letters</i> , 2016 , 109, 121102	3.4	43
52	Low temperature electron mobility exceeding 104 cm ² /V s in MOCVD grown β -Ga ₂ O ₃ . <i>APL Materials</i> , 2019 , 7, 121110	5.7	42
51	Solar blind Schottky photodiode based on an MOCVD-grown homoepitaxial β -Ga ₂ O ₃ thin film. <i>APL Materials</i> , 2019 , 7, 022527	5.7	41
50	High Al-Content AlGa _N Transistor With 0.5 A/mm Current Density and Lateral Breakdown Field Exceeding 3.6 MV/cm. <i>IEEE Electron Device Letters</i> , 2018 , 39, 256-259	4.4	40
49	Effect of buffer iron doping on delta-doped β -Ga ₂ O ₃ metal semiconductor field effect transistors. <i>Applied Physics Letters</i> , 2018 , 113, 123501	3.4	39
48	GaN-based three-junction cascaded light-emitting diode with low-resistance InGa _N tunnel junctions. <i>Applied Physics Express</i> , 2015 , 8, 082103	2.4	37
47	Low-resistance Ga _N tunnel homojunctions with 150 kA/cm ² current and repeatable negative differential resistance. <i>Applied Physics Letters</i> , 2016 , 108, 131103	3.4	37
46	Graded AlGa _N Channel Transistors for Improved Current and Power Gain Linearity. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3114-3119	2.9	35
45	Low 10 ¹⁴ cm ⁻³ free carrier concentration in epitaxial β -Ga ₂ O ₃ grown by MOCVD. <i>APL Materials</i> , 2020 , 8, 021110	5.7	34
44	Design of p-type cladding layers for tunnel-injected UV-A light emitting diodes. <i>Applied Physics Letters</i> , 2016 , 109, 191105	3.4	28
43	Investigation of unintentional Fe incorporation in (010) β -Ga ₂ O ₃ films grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2019 , 115, 052102	3.4	27
42	Reflective metal/semiconductor tunnel junctions for hole injection in AlGa _N UV LEDs. <i>Applied Physics Letters</i> , 2017 , 111, 051104	3.4	26
41	Electro-thermal co-design of β -(Al _x Ga _{1-x}) ₂ O ₃ /Ga ₂ O ₃ modulation doped field effect transistors. <i>Applied Physics Letters</i> , 2020 , 117, 153501	3.4	25
40	Modeling and analysis for thermal management in gallium oxide field-effect transistors. <i>Journal of Applied Physics</i> , 2020 , 127, 154502	2.5	25
39	Anisotropic etching of β -Ga ₂ O ₃ using hot phosphoric acid. <i>Applied Physics Letters</i> , 2019 , 115, 013501	3.4	23
38	Enhanced light extraction in tunnel junction-enabled top emitting UV LEDs. <i>Applied Physics Express</i> , 2016 , 9, 052102	2.4	23
37	Metal oxide catalyzed epitaxy (MOCATAXY) of β -Ga ₂ O ₃ films in various orientations grown by plasma-assisted molecular beam epitaxy. <i>APL Materials</i> , 2020 , 8, 021104	5.7	21

36	Near unity ideality factor for sidewall Schottky contacts on un-intentionally doped AlGa_2O_3 . <i>Applied Physics Express</i> , 2019 , 12, 044005	2.4	17
35	Sn doping of (010) AlGa_2O_3 films grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020 , 117, 222102	3.4	16
34	Metalorganic chemical vapor deposition grown n-InGaN/n-GaN tunnel junctions for micro-light-emitting diodes with very low forward voltage. <i>Semiconductor Science and Technology</i> , 2020 , 35, 125023	1.8	16
33	Dielectric function tensor (1.5 eV to 9.0 eV), anisotropy, and band to band transitions of monoclinic $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ ($x = 0.21$) films. <i>Applied Physics Letters</i> , 2019 , 114, 231901	3.4	15
32	2D Materials for Universal Thermal Imaging of Micro- and Nanodevices: An Application to Gallium Oxide Electronics. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2945-2953	4	14
31	Orientation-dependent band offsets between $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ and Ga_2O_3 . <i>Applied Physics Letters</i> , 2020 , 117, 252104	3.4	14
30	Atomic scale investigation of chemical heterogeneity in $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ films using atom probe tomography. <i>Applied Physics Letters</i> , 2019 , 115, 132105	3.4	13
29	Ultralow-voltage-drop GaN/InGaN/GaN tunnel junctions with 12% indium content. <i>Applied Physics Express</i> , 2017 , 10, 121003	2.4	13
28	Design of compositionally graded contact layers for MOCVD grown high Al-content AlGaIn transistors. <i>Applied Physics Letters</i> , 2019 , 115, 043502	3.4	12
27	RF operation in graded $\text{Al}_x\text{Ga}_{1-x}\text{In}$ ($x = 0.65$ to 0.82) channel transistors. <i>Electronics Letters</i> , 2018 , 54, 1351-1353	1.1	11
26	H_2O vapor assisted growth of AlGa_2O_3 by MOCVD. <i>AIP Advances</i> , 2020 , 10, 085002	1.5	10
25	Thermal management strategies for gallium oxide vertical trench-fin MOSFETs. <i>Journal of Applied Physics</i> , 2021 , 129, 085301	2.5	10
24	Recent progress of tunnel junction-based ultra-violet light emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC0805	1.4	9
23	Effect of Grain Boundary Scattering on Electron Mobility of N-Polarity InN Films. <i>Applied Physics Express</i> , 2013 , 6, 021001	2.4	9
22	Formation of p-n-p junction with ionic liquid gate in graphene. <i>Applied Physics Letters</i> , 2014 , 104, 143102	3.4	8
21	Importance of shallow hydrogenic dopants and material purity of ultra-wide bandgap semiconductors for vertical power electron devices. <i>Semiconductor Science and Technology</i> , 2020 , 35, 125018	1.8	8
20	Current gain in sub-10 nm base GaN tunneling hot electron transistors with AlN emitter barrier. <i>Applied Physics Letters</i> , 2015 , 106, 032101	3.4	7
19	Current gain above 10 in sub-10 nm base III-Nitride tunneling hot electron transistors with GaN/AlN emitter. <i>Applied Physics Letters</i> , 2016 , 108, 192101	3.4	6

18	Epitaxial growth of AlGa_2O_3 on (110) substrate by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020 , 117, 152105	3.4	5
17	Sub 300 nm wavelength III-Nitride tunnel-injected ultraviolet LEDs 2015 ,		4
16	An approach to high open-circuit voltage polymer solar cells via alcohol/water-soluble cathode interlayers based on anthrathiadiazole derivatives. <i>New Journal of Chemistry</i> , 2017 , 41, 13166-13174	3.6	3
15	Point Defect and Their Influence on the Atomic and Electronic Structure of $\text{Al}(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ Alloys by STEM-EELS. <i>Microscopy and Microanalysis</i> , 2020 , 26, 622-623	0.5	2
14	Small-signal characteristics of graded AlGa _N channel PoFETs 2017 ,		2
13	AlGa_2O_3 lateral transistors with high aspect ratio fin-shape channels. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 014001	1.4	2
12	Design and Demonstration of $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3/\text{Ga}_2\text{O}_3$ Double Heterostructure Field Effect Transistor (DHFET) 2018 ,		2
11	Mg doping and diffusion in (010) AlGa_2O_3 films grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2021 , 130, 235301	2.5	2
10	Common Emitter Current and Voltage Gain in III-Nitride Tunneling Hot Electron Transistors. <i>IEEE Electron Device Letters</i> , 2015 , 36, 436-438	4.4	1
9	N-polar III-nitride tunneling hot electron transfer amplifier 2014 ,		1
8	Thermal Management of AlGa_2O_3 Current Aperture Vertical Electron Transistors. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2021 , 11, 1171-1176	1.7	1
7	Molecular beam epitaxy of GaN on 2HMoS_2 . <i>Applied Physics Letters</i> , 2020 , 117, 123102	3.4	0
6	Recent Progress in III-Nitride Tunnel Junction-Based Optoelectronics. <i>International Journal of High Speed Electronics and Systems</i> , 2019 , 28, 1940012	0.5	0
5	Zeeman spin-splitting in the (010) AlGa_2O_3 two-dimensional electron gas. <i>Applied Physics Letters</i> , 2019 , 115, 262103	3.4	0
4	III-Nitride Tunneling Hot Electron Transfer Amplifier (THETA) 2020 , 109-157		0
3	Field-Effect Transistors 3. <i>Springer Series in Materials Science</i> , 2020 , 609-621	0.9	
2	Electron effective mass determination across a $\text{Al}_{0.2}\text{Ga}_{0.8}\text{O}_3/\text{AlGa}_2\text{O}_3$ interface by Kramers-Kronig analysis. <i>Microscopy and Microanalysis</i> , 2021 , 27, 1168-1169	0.5	
1	Tight-binding band structure of Γ and Γ_5 phase Ga_2O_3 and Al_2O_3 . <i>Journal of Applied Physics</i> , 2022 , 131, 175702	2.5	

